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**Complete if Known**

<b>Application Number</b>	<b>9/992,560</b>
<b>Filing Date</b>	<b>November 5, 2001</b>
<b>First Name of Inventor</b>	<b>KENNETH E. GONSALVES</b>
<b>Group Art Unit</b>	<b>1752</b>
<b>Examiner Name</b>	
<b>Attorney Docket Number</b>	<b>46872-257422</b>

Sheet	1	of	2
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## U.S. PATENT DOCUMENTS

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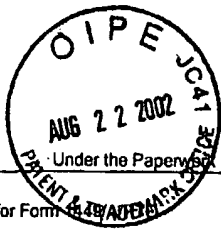
## FOREIGN PATENT DOCUMENTS

**Examiner  
Signature**

Date  
Considered

10-28-04

<sup>1</sup>Unique citation designation number. <sup>2</sup>See attached Kinds of U.S. Patent Documents. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent document, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language translation is attached.



Substitute for Form 1449		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)		Application Number	09/992,560
		Filing Date	November 15, 2001
		First Name and Inventor	KENNETH E. GONSALVES
		Group Art Unit	1752
		Examiner Name	
Sheet 2	of 2	Attorney Docket Number	46872-257422

OTHER INFORMATION - NON PATENT LITERATURE DOCUMENTS		
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published
SJL		KENNETH E. GONSALVES, et al., "Combinatorial approach for the synthesis of terpolymers and their novel application as very-high-contrast resists for x-ray nanolithography," J. Vac. Sci. Technol. B 18(1), Jan/Feb 2000, pp. 325-327.
		YOUNQI HU, et al., "Nanocomposite resists for electron beam nanolithography," Microelectronic Engineering 56 (2001), pp. 289-294.
		HENPENG WU, et al., "Incorporation of polyhedral oligosilsesquioxane in chemically amplified resists to improve their reactive ion etching resistance," J. Vac. Sci. Technol. B 19(3), May/Jun 2001, pp. 851-855.
		HENGPENG WU, et al., "Synthesis and Characterization of Radiation-sensitive Polymers and Their Application in Lithography," Ph.D. dissertation, University of Connecticut, April 2001.
		L. MERHARI, et al., "Nanocomposite resist systems for next generation lithography," Microelectronic Engineering (2002), article in press.
		JOHN CANNING, "Next generation Lithography: When, why, and at what cost?" Microelectronic Engineering (2002), article in press, abstract only.
		ROBERT L. BRAINARD, "Resists for next generation lithography," Microelectronic Engineering (2002), article in press.
		SATOSHI SAITO, "A new positive electron-beam resist material composed of catechol derivatives," Microelectronic Engineering (2002), article in press.
		HENGPENG WU, et al., "Preparation of a Photoacid Generating Monomer and Its Application in Lithography," Advanced Functional Materials, 11(4), August 2001, pp. 271-276.
		HENGPENG WU, et al., "A Novel Single-Component Negative Resist for DUV and Electron Beam Lithography," Advanced Functional Materials, 13(3), February 2001, pp. 195-197.

Examiner Signature	<i>Su J. Lee</i>	Date Considered	10-28-2004
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<sup>1</sup>Unique citation designation number. <sup>2</sup>Applicant is to place a check mark here if English language translation is attached.